

Alexey Sherchenkov

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Low power reconfigurable multilevel nanophotonic devices based on Sn-doped Ge ₂ Sb ₂ Te ₅ thin films. <i>Acta Materialia</i> , 2022, 234, 117994.	7.9	11
2	Specific Features of Formation of Laser-Induced Periodic Surface Structures on Ge ₂ Sb ₂ Te ₅ Amorphous Thin Films under Illumination by Femtosecond Laser Pulses. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900617.	1.5	13
3	Influence of the adjacent layers on the crystallization kinetics of Ge ₂ Sb ₂ Te ₅ thin films. <i>Journal of Thermal Analysis and Calorimetry</i> , 2020, 142, 1019-1029.	3.6	3
4	Kinetics of volume and surface driven crystallization in thin films. <i>Journal of Physics Condensed Matter</i> , 2020, 32, 355401.	1.8	3
5	Influence of the Degree of Crystallinity on the Dispersion of the Optical Parameters of Ge ₂ Sb ₂ Te ₅ Phase-Change Memory Thin Films. <i>Semiconductors</i> , 2020, 54, 1775-1783.	0.5	4
6	The vacuum arc ion source for indium and tin ions implantation into phase change memory thin films. <i>Review of Scientific Instruments</i> , 2019, 90, 123313.	1.3	2
7	Laser-induced modification and formation of periodic surface structures (ripples) of amorphous GST ₂₂₅ phase change materials. <i>Optics and Laser Technology</i> , 2019, 113, 87-94.	4.6	18
8	Multiple thermal cycling and phase transitions in Ge-Sb-Te materials. <i>Journal of Non-Crystalline Solids</i> , 2018, 501, 101-105.	3.1	1
9	Characteristics of Amorphous As ₂ S ₃ Semiconductor Films Obtained via Spin Coating. <i>Semiconductors</i> , 2018, 52, 1963-1968.	0.5	1
10	The Influence of Materials of Electrodes of Sensitized Solar Cells on Their Capacitive and Electrical Characteristics. <i>Russian Physics Journal</i> , 2018, 61, 196-202.	0.4	3
11	The influence of compression conditions on the peculiarities of self-propagating exothermal reaction in Al-Ni powder reactive materials. <i>Journal of Thermal Analysis and Calorimetry</i> , 2018, 134, 35-44.	3.6	5
12	Effect of doping on the crystallization kinetics of phase change memory materials on the basis of Ge-Sb-Te system. <i>Journal of Thermal Analysis and Calorimetry</i> , 2017, 127, 283-290.	3.6	15
13	Electrophysical Properties of Ge-Sb-Te Thin Films for Phase Change Memory Devices. <i>Russian Physics Journal</i> , 2017, 59, 1417-1424.	0.4	2
14	Integral isoconversional method for evaluating crystallization parameters of thin films of Ge ₂ Sb ₂ Te ₅ phase change memory materials. <i>Inorganic Materials</i> , 2017, 53, 45-49.	0.8	1
15	Electrical properties and transport mechanisms in phase change memory thin films of quasi-binary-line GeTe-Sb ₂ Te ₃ chalcogenide semiconductors. <i>Semiconductors</i> , 2017, 51, 146-152.	0.5	2
16	Peculiarities of Bi doping of Ge-Sb-Te thin films for PCM devices. <i>Canadian Journal of Physics</i> , 2014, 92, 684-689.	1.1	20
17	Estimation of kinetic parameters for the phase change memory materials by DSC measurements. <i>Journal of Thermal Analysis and Calorimetry</i> , 2014, 117, 1509-1516.	3.6	21
18	Thermal properties of phase change material Ge ₂ Sb ₂ Te ₅ doped with Bi. <i>Journal of Non-Crystalline Solids</i> , 2013, 377, 26-29.	3.1	17

#	ARTICLE	IF	CITATIONS
19	Thermal effects in Ge-Sb-Te phase- change memory materials during multiple thermal cycling. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, NA-NA.	0.8	14